

Monday, September 26									
13:00-17:30 Short Course A (201) : Scaling and monolithic vs. heterogeneous integration for advanced, future technology nodes Short Course B (301) : Recent advances in ultra-wide-bandgap semiconductors									
Tuesday, September 27									
9:00-11:10 (Convention Hall) : Opening & Award Ceremony & Plenary Session 1									
101	102	103	104	105	201	301	302	303	304
		11:30 ~ 12:15 [C-1] Energy Harvesting Devices	11:30 ~ 12:30 [D-1] Micro/Nano Technologies for Biosensing and Interfaces	11:30 ~ 12:45 [E-1] Emerging Thin Film Devices and Technologies	11:30 ~ 12:30 [F-1] Ferroelectric Memory Materials	11:30 ~ 12:45 [G-1] Cryo-CMOS	11:30 ~ 12:30 [H-1] Characterization I: Low Dimensional Devices and Materials	11:30 ~ 12:30 [J-1] Advanced Technologies for GaN Devices	11:30 ~ 12:30 [K-1] 3D Integration and Advanced Packaging I
Lunch Break									
14:00 ~ 15:30 [A-2] New Materials and Platforms for Photonics	14:00 ~ 15:45 [B-2] Wide Bandgap Materials	14:00 ~ 15:30 [C-2] Inorganic Semiconductor Materials & Applications	14:00 ~ 15:45 [D-2] Biosensor, Chips and Microfluidic Devices for Cell Functions	14:00 ~ 16:00 [E-2] Advanced Group IV Thin Film Devices and Technologies	14:00 ~ 15:30 [F-2] PCM, MRAM, and RRAM	14:00 ~ 16:00 [G-2] Modeling, Simulation and Characterization	14:00 ~ 15:45 [H-2] Novel Function Devices	14:00 ~ 15:30 [J-2] GaN-based High-speed Devices	14:00 ~ 15:15 [K-2] Advanced Sensor Systems
Break									
	16:15 ~ 18:00 [B-3] Group IV Materials I	16:15 ~ 18:00 [C-3] Perovskite Solar Cells	16:15 ~ 18:00 [D-3] Advanced Technologies for Bio- and Chemical Sensing	16:15 ~ 18:00 [E-3] Oxide Semiconductor TFT	16:15 ~ 18:00 [F-3] Ferroelectric Devices	16:15 ~ 17:45 Area1&2&9 [G-3] Quantum Computing I Focus Session 1	16:15 ~ 18:00 [H-3] Characterization II: Low Dimensional Devices and Materials	16:15 ~ 17:45 [J-3] High-speed Devices	16:15 ~ 17:45 Area3&5&12 [K-3] Design, Process, and Technology for High-performance Chiplet I Focus Session 3
Break									
18:30-20:30 (Convention Hall) : Complimentary Reception * On-site Event									
Wednesday, September 28									
101	102	103	104	105	201	301	302	303	304
		09:00 ~ 10:15 [C-4] Battery, Photocatalyst, Photodetector		09:00 ~ 11:15 Area1&10 [E-4] Oxide Semiconductors for Logic and Memory Applications Joint Session	09:00 ~ 10:15 [F-4] Emerging Memory Devices	09:00 ~ 10:15 Area1&2&9 [G-4] Quantum Computing II Focus Session 1	09:00 ~ 10:00 [H-4] Device Application I: Low Dimensional Devices and Materials	09:00 ~ 10:15 [J-4] Ultrawide Bandgap Semiconductor Devices	09:00 ~ 10:15 [K-4] Design, Process, and Technology for High-performance Chiplet II/3D Integration and Advanced Packaging II
Break									
10:45 ~ 12:15 [A-5] UV Sources and Detectors	10:45 ~ 12:00 [B-5] Advanced Materials, Nanofabrication and Thin Films I	10:45 ~ 12:00 Area1&2&9 [C-5] Quantum Computing III Focus Session 1	10:45 ~ 12:15 [D-5] Transistor Technologies for Biological and Electrochemical Applications		10:45 ~ 12:00 [F-5] 3D NAND Flash Memory	10:45 ~ 12:15 [G-5] Image Sensor Technology	10:45 ~ 11:45 [H-5] Device Application II: Low Dimensional Devices and Materials	10:45 ~ 12:00 [J-5] SiC Processes and Characterizations	10:45 ~ 12:00 [K-5] Advanced Neuron and AI Systems
Lunch Break									
13:30 ~ 15:45 [A-6] III-V Light Sources	13:30 ~ 15:15 [B-6] Advanced Materials, Nanofabrication and Thin Films II	13:30 ~ 15:30 Area1&2&9 [C-6] Quantum Computing IV Focus Session 1	13:30 ~ 15:30 [D-6] Functional Devices and Application	13:30 ~ 15:30 [E-6] Advanced Oxide Sensors	13:30 ~ 15:00 [F-6] Charge-Based Memory Devices for AI Applications	13:30 ~ 15:15 Area1&2 [G-6] Ferroelectric Devices Joint Session	13:30 ~ 15:00 [H-6] Growth and Synthesis: Low Dimensional Devices and Materials	13:30 ~ 15:45 [J-6] Interface Technologies	13:30 ~ 15:30 [K-6] MEMS and Advanced Metallization I
Break									
16:00-17:30 (Convention Hall) : Plenary Session 2									
Break									
18:00-20:00 (Convention Hall) : Rump Session * On-site Event									
Thursday, September 29									
101	102	103	104	105	201	301	302	303	304
				9:00 ~ 10:45 [E-7] MEMS and Advanced Metallization II	09:00 ~ 10:15 [F-7] In-Memory and Unconventional Computing	09:00 ~ 10:15 [G-7] Advanced CMOS: Device Technology			09:00 ~ 10:15 [K-7] Advanced Systems with Innovative Devices
Break									
	10:45 ~ 12:00 [B-8] Group IV Materials II	10:45 ~ 12:00 [C-8] Spintronics I	10:45 ~ 12:00 [D-8] Optoelectronics and Thermoelectronic Devices		10:45 ~ 12:00 [F-8] Memory Devices for New Applications	10:45 ~ 11:45 [G-8] Ferroelectric Material and Process	10:45 ~ 12:00 [H-8] Device Application III: Low Dimensional Devices and Materials	10:45 ~ 12:00 [J-8] Si and SiC Power Devices	10:45 ~ 12:00 Area1&12 [K-8] Innovative Devices and Systems for Advanced Imaging and Sensing Joint Session
Lunch Break									
13:30 ~ 15:15 [A-9] Imaging Sensors and Detectors		13:30 ~ 15:30 [C-9] Thermoelectric Devices			13:30 ~ 15:15 Area1&2&8 [F-9] CMOS and Memory Applications of Low Dimensional Materials I Focus Session 2			13:30 ~ 15:00 [J-9] GaN Power Devices	13:30 ~ 15:15 [K-9] Advanced Device-based Circuits and Power Management Systems
Break									
16:00 ~ 18:00 [A-10] Integrated Photonic Devices		16:00 ~ 17:30 [C-10] Spintronics II			16:00 ~ 17:45 Area1&2&8 [F-10] CMOS and Memory Applications of Low Dimensional Materials II Focus Session 2	16:00 ~ 18:00 [G-10] Advanced CMOS: Device, Process and Material		16:00 ~ 17:45 [J-10] DRAM, SRAM, and 3D NAND	

Area Scope	Area
	Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology
	Area 2: Advanced and Emerging Memories / New Applications
	Area 3: Interconnect / 3D Integrations / MEMS
	Area 4: Power / High-speed Devices and Materials
	Area 5: Photonics: Devices / Integration / Related Technology
	Area 6: Photovoltaics / Energy Harvesting / Battery-related Technology

Area Scope	Area
	Area 7: Organic / Molecular / Bio-electronics
	Area 8: Low Dimensional Devices and Materials
	Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
	Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
	Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
	Area 12: Advanced Circuits / Systems Interacting with Innovative Devices and Materials